

CMOS

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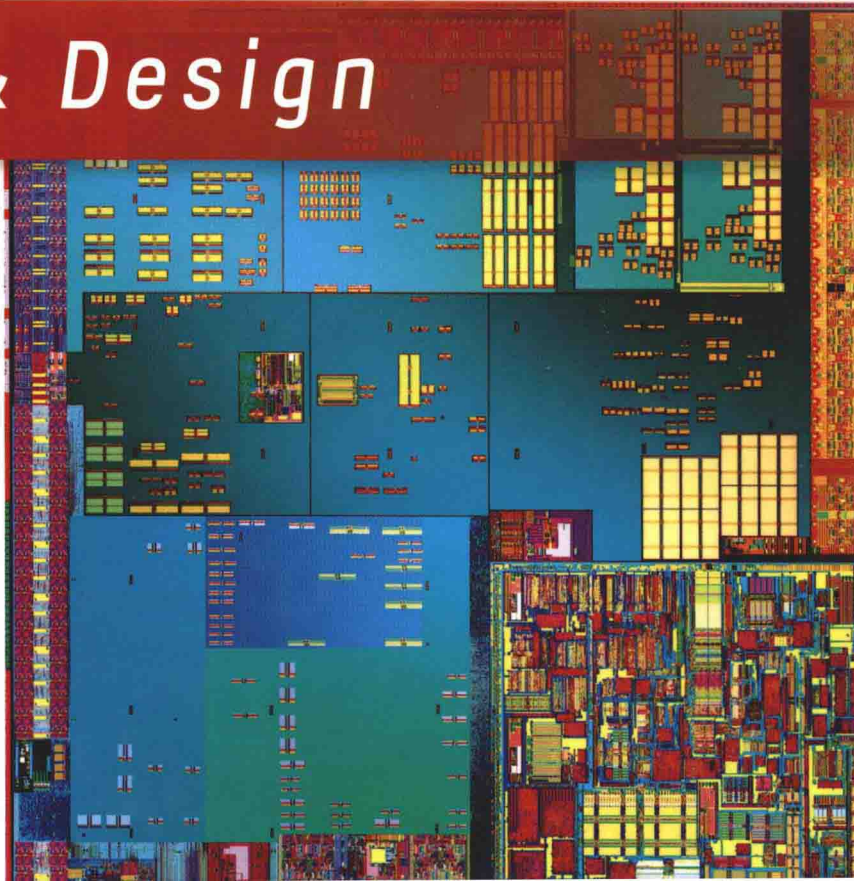
Digital Integrated Circuits

Analysis & Design

Sung-Mo Kang

Yusuf Leblebici

Chulwoo Kim



CMOS Digital Integrated Circuits

Analysis and Design

Fourth Edition

Sung-Mo (Steve) Kang

*Korea Advanced Institute of Science and Technology
University of California at Santa Cruz*

Yusuf Leblebici

Swiss Federal Institute of Technology – Lausanne

Chulwoo Kim

Korea University – Seoul

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CMOS Digital Integrated Circuits

ABOUT THE AUTHORS

Sung-Mo “Steve” Kang received his PhD in electrical engineering from the University of California, Berkeley. He has worked on the development of full-custom CMOS VLSI chips, including the world’s first 32-bit full CMOS microprocessor and peripheral chips at AT&T Bell Laboratories in Murray Hill, New Jersey. He has taught digital integrated circuits at the University of Illinois at Urbana-Champaign; the University of California, Santa Cruz; the University of California, Merced; and the Korea Advanced Institute of Science and Technology (KAIST) in Daejeon, Korea. He has also given invited lectures and tutorials on CMOS digital circuits, reliability, and computer-aided design of VLSI circuits and systems at major conferences and universities globally.

Dr. Kang is a fellow of IEEE, ACM, and AAAS and has received many awards, including the IEEE Millennium Medal, IEEE Graduate Teaching Technical Field Award, IEEE CAS Society M. E. Van Valkenburg Award, IEEE CAS Society Technical Excellence Award, SRC Technical Excellence Award, and Chang-Lin Tien Education Leadership Award. He has served as Department Head of the University of Illinois at Urbana-Champaign; Dean of Engineering at the University of California, Santa Cruz; Chancellor of the University of California, Merced; and President of KAIST, Daejeon, Korea.

Yusuf Leblebici received a PhD in electrical and computer engineering from the University of Illinois at Urbana-Champaign. He has been a visiting assistant professor of electrical and computer engineering at the University of Illinois at Urbana-Champaign, associate professor of electrical and electronics engineering at Istanbul Technical University, and associate professor of electrical and computer engineering at Worcester Polytechnic Institute. He also served as the microelectronics program coordinator at Sabanci University. Currently, he is a full (chair) professor at the Swiss Federal Institute of Technology in Lausanne, Switzerland, and director of the Microelectronic Systems Laboratory. His research interests include design of high-performance CMOS digital and mixed-signal integrated circuits, computer-aided design of VLSI systems, intelligent sensor interfaces, modeling and simulation of semiconductor devices, and VLSI reliability analysis. He is a fellow of IEEE and recipient of the NATO Science Fellowship Award, the Young Scientist Award of the Turkish Scientific and Technological Research Council, and the Joseph Samuel Satin Distinguished Fellow Award of the Worcester Polytechnic Institute. He was elected as Distinguished Lecturer of the IEEE Circuits and Systems Society for 2010–2011.

Chulwoo Kim received BS and MS degrees in electronics engineering from Korea University, and a PhD in electrical and computer engineering from the University of Illinois at Urbana-Champaign. In 1999, he worked as a summer intern at

Design Technology at Intel Corporation, Santa Clara, California. In May 2001, he joined IBM Microelectronics Division in Austin, Texas, where he was involved in cell processor design. Since September 2002, he has been with the Department of Electronics and Computer Engineering at Korea University, where he is currently a professor. He was a visiting professor at the University of California, Los Angeles and at the University of California, Santa Cruz. His current research interests are in the areas of wireline transceiver, memory, power management, and data converters.

Dr. Kim received the Samsung HumanTech Thesis Contest Bronze Award, the ISLPED Low-Power Design Contest Award, the DAC Student Design Contest Award, the SRC Inventor Recognition Award, the Young Scientist Award from the Ministry of Science and Technology of Korea, the Seoktop Award for excellence in teaching, and the ASP-DAC Best Design Award. He is currently on the editorial board of *IEEE Transactions on VLSI Systems* and on the Technical Program Committee of the IEEE International Solid-State Circuits Conference.

PREFACE

Complementary metal oxide semiconductor (CMOS) digital integrated circuits are the enabling technology for the modern information age. Because of their intrinsic features in low-power consumption, large noise margins, and ease of design, CMOS integrated circuits have been widely used to develop random access memory (RAM) chips, microprocessor chips, digital signal processor (DSP) chips, and application-specific integrated circuit (ASIC) chips. The popular use of CMOS circuits continues to grow with the increasing demands for low-power, low-noise integrated electronic systems in the development of mobile computing platforms, wearable communication devices, smart phones, and multimedia systems.

Since the field of CMOS integrated circuits is broad, it is conventionally divided into digital CMOS circuits and analog CMOS circuits. This textbook is focused on the CMOS digital integrated circuits. However, it should be noted that the boundary between classical digital and analog CMOS design is becoming increasingly blurred, especially with the challenges presented by nanometer-scale fabrication technologies, very low operating voltages, and operating frequencies extending well into the multi-GHz range. Therefore, we attempt to present the analysis and design of digital CMOS integrated circuits from an “analog” point-of-view, i.e., taking into account the analog, non-discrete nature of the devices and circuits that are used to implement digital functions.

The origins of this textbook date back to the early 1990s, when the first two authors were intensively involved in undergraduate- and graduate-level teaching of digital IC fundamentals. At the University of Illinois at Urbana-Champaign, where both of us were teaching at the time, we tried some of the available textbooks on digital MOS integrated circuits for our senior-level technical elective course, ECE382—Large Scale Integrated Circuit Design. Students and instructors alike realized, however, that there was a need for a new book with more comprehensive treatment of CMOS digital circuits. Thus, our textbook project was initiated several years ago by assembling our own lecture notes. Since 1993, we have used evolving versions of this material at the University of Illinois at Urbana-Champaign, at Istanbul Technical University, at Worcester Polytechnic Institute, and at the Swiss Federal Institute of Technology in Lausanne. We are both encouraged by comments from our students, colleagues, and reviewers. The first edition of *CMOS Digital Integrated Circuits: Analysis and Design* was published in late 1995.

Soon after publishing the first edition, we saw the need for updating it to reflect the many constructive comments we were receiving from instructors and students who used the textbook. We intended to include and update important topics such as low-power circuit design and interconnects in high-speed circuit design, as well as the deep sub-micron circuit design issues, and to provide more rigorous treatment of new developments in memory circuits. We also felt that in a rapidly developing field such as CMOS

digital circuits, the quality of a textbook can only be preserved by timely updates reflecting the state of the art. This realization has led us to embark on the successive revisions of our work, with the second edition appearing in 1998 and the third edition in 2002, to reflect the advances in technology and in circuit design practices.

During the 11 years that have passed since the publication of the third edition in 2002, the domain of CMOS digital integrated circuits has continued to grow and develop at an ever-increasing pace. The advent of nanometer-scale technologies and the widespread use of system-on-chip architectures combining a large number of functional blocks on chip have ushered in dramatic changes in the way digital CMOS integrated circuit design has to be treated. Thus, we came to the conclusion that incremental revisions would no longer do justice for the next edition of this textbook, and that we needed a comprehensive rewriting of virtually all chapters. The author team was expanded by the valuable addition of Professor Chulwoo Kim of Korea University, and an extensive revision was embarked upon. The fourth edition is the outcome of this intensive effort.

CMOS Digital Integrated Circuits: Analysis and Design is intended primarily as a comprehensive textbook at the senior level and first-year graduate level, as well as a reference for practicing engineers in the areas of integrated circuit design, digital design, and VLSI. Recognizing that the area of digital integrated circuit design is evolving at an increasingly faster pace, we have made our best effort to present up-to-date materials on all subjects covered. This textbook contains 15 chapters; we recognize that it would not be possible to cover rigorously all of this material in one semester. Thus, we would propose the following based on our teaching experience: At the undergraduate level, coverage of the first 10 chapters would constitute sufficient material for a one-semester course on CMOS digital integrated circuits.

Time permitting, some selected topics in Chapter 11, “Low-Power CMOS Logic Circuits,” Chapter 12, “Arithmetic Building Blocks,” and Chapter 13, “Clock and I/O Circuits” could also be covered. Alternatively, this book could be used for a two-semester course, allowing a more detailed treatment of advanced issues, which are presented in the later chapters. At the graduate level, selected topics from the first 10 chapters plus the last 5 chapters can be covered in one semester.

The first 8 chapters of this textbook are devoted to a detailed treatment of the MOS transistor with all its relevant aspects; to the static and dynamic operation principles, analysis, and design of basic inverter circuits; and to the structure and operation of combinational and sequential logic gates. Note that the introduction chapter has been significantly expanded to include a detailed presentation of VLSI design methodologies. Since the digital integrated circuit design techniques discussed in the first half of this textbook are directly relevant for digital VLSI and ASIC design, we felt that the context should be presented at the beginning of the book. The issues of on-chip interconnect modeling and interconnect delay calculation are covered extensively in Chapter 6, which provides a complete view of switching characteristics in digital integrated circuits. A separate chapter (Chapter 9) has been reserved for the treatment of dynamic logic circuits, which are used in state-of-the-art VLSI chips. Chapter 10 has been completely revised in both content and presentation; it offers an in-depth presentation of many state-of-the-art semiconductor memory circuits.

Recognizing the increasing importance of low-power circuit design, we dedicate one chapter (Chapter 11) to low-power CMOS logic circuits, which provides a comprehensive coverage of methodologies and design practices that are used to reduce the power dissipation of large-scale digital integrated circuits. Key arithmetic building blocks are presented in Chapter 12, with an emphasis on high-performance multi-bit adders and multipliers.

Next, Chapter 13 provides a clear insight into the important subjects of clocking and chip I/O design. Critical issues such as ESD protection, clock distribution, clock buffering, and latch-up phenomena are discussed in detail. Finally, the more advanced but important topics of design for manufacturability and design for testability are covered in Chapters 14 and 15, respectively.


We have long debated the coverage of nMOS circuits in this textbook. We have concluded that some coverage should be provided for pedagogical reasons. Thus, to emphasize the load concept, which is still widely used in many areas in digital circuit design, we present basic resistive-load and pseudo-nMOS inverter circuits along with their CMOS counterparts in Chapter 5, while we present pseudo-nMOS logic gates (NAND/NOR) in Chapter 7.

The Online Learning Center for this edition (www.mhhe.com/kang) also contains:

- An Instructors Manual
- Lecture Slides (PowerPoint and PDF)
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Although an immense amount of effort and attention to detail were expended to prepare the camera-ready manuscript, this textbook may still have some flaws and

mistakes due to erring human nature. We welcome and greatly appreciate suggestions and corrections from readers for the improvement of technical content as well as the presentation style.

ACKNOWLEDGMENTS TO THE FIRST EDITION

Our colleagues have provided many constructive comments and encouragement for the completion of the first edition. Professor Timothy N. Trick, former head of the department of electrical and computer engineering at the University of Illinois at Urbana-Champaign, has strongly supported our efforts from the very beginning. The appointment of Sung-Mo Kang as an associate in the Center for Advanced Study at the University of Illinois at Urbana-Champaign helped to start the process. Yusuf Leblebici acknowledges the full support and encouragement from the department of electrical and electronics engineering at Istanbul Technical University, where he introduced a new digital integrated circuits course based on the early version of this book and received very valuable feedback from his students.

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Sung-Mo (Steve) Kang
Daejeon, Korea
August 2013

Yusuf Leblebici
Lausanne, Switzerland
August 2013

Chluwoo Kim
Seoul, Korea
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